COMPLEMENTARY PAIR ENHANCEMENT MODE MOSFET

Product Summary

Device	$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D MAX T_A = +25°C
Q1 N-Channel	20V	40mΩ @ V_{GS} = 4.5V	4.7A
		65mΩ @ V_{GS} = 2.5V	3.7A
Q2 P-Channel	-20V	90mΩ @ V_{GS} = -4.5V	-3.2A
		137mΩ @ V_{GS} = -2.5V	-2.6A

Features

- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Max Height
- **ESD protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

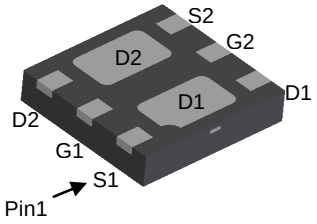
- Load Switch
- Power Management Functions
- Portable Power Adaptors

Mechanical Data

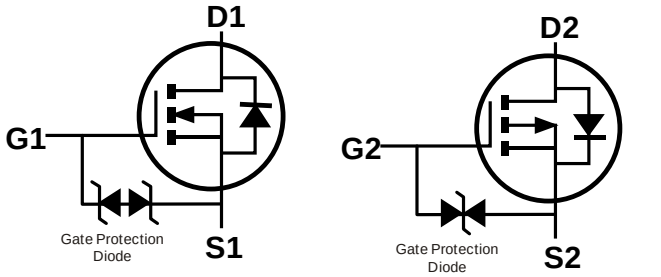
- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 e4
- Terminal Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)

ESD PROTECTED

U-DFN2020-6



Bottom View



Q1 N-CHANNEL MOSFET O2 P-CHANNEL MOSFET

Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMC2041UFDB -7	U-DFN2020-6	3,000/Tape & Reel
DMC2041UFDB -13	U-DFN2020-6	10,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

U-DFN2020-6

D4 = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: B = 2014)
M = Month (ex: 9 = September)

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020
Code	B	C	D	E	F	G	H

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Q1 N-CHANNEL	Q2 P-CHANNEL	Units
Drain-Source Voltage			V_{DSS}	20	-20	V
Gate-Source Voltage			V_{GSS}	±12	±12	V
Continuous Drain Current (Note 5) V_{GS} = 4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	4.7 3.8	-3.2 -2.5	A
	t < 5s	T_A = +25°C T_A = +70°C	I_D	6.1 4.9	-4.1 -3.2	A
Maximum Continuous Body Diode Forward Current (Note 5)			I_S	2	-1.5	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I_{DM}	30	-18	A

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	Steady State	P_D	1.4	W
	t < 5s		2.2	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	92	°C/W
	t < 5s		55	
Thermal Resistance, Junction to Case (Note 5)		$R_{\theta JC}$	30	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Electrical Characteristics Q1 N-CHANNEL (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	1.0	µA	V_{DS} = 20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(th)}$	0.35	—	1.4	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	23	40	mΩ	V_{GS} = 4.5V, I_D = 4.2A
		—	26	65		V_{GS} = 2.5V, I_D = 3.3A
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	V_{GS} = 0V, I_S = 4.4A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	713	—	pF	V_{DS} = 10V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	80	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	68	—	pF	
Gate Resistance	R_g	—	15	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	8	—	nC	V_{DS} = 10V, I_D = 5.5A
Total Gate Charge (V_{GS} = 8V)		—	15	—	nC	
Gate-Source Charge	Q_{gs}	—	1.0	—	nC	
Gate-Drain Charge	Q_{gd}	—	1.1	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	3.6	—	ns	V_{DD} = 10V, V_{GS} = 4.5V, R_L = 2.3Ω, R_G = 1Ω
Turn-On Rise Time	t_r	—	15.9	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	16.0	—	ns	
Turn-Off Fall Time	t_f	—	2.6	—	ns	
Body Diode Reverse Recovery Time	trr	—	6.6	—	nS	I_S = 4.4A, dI/dt = 100A/µs
Body Diode Reverse Recovery Charge	Qrr	—	1.2	—	nC	I_S = 4.4A, dI/dt = 100A/µs

Notes: 5. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.

Electrical Characteristics Q2 P-CHANNEL (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	-20	—	—	V	V_{GS} = 0V, I_D = -250μA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	-1.0	μA	V_{DS} = -20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	μA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.35	—	-1.4	V	V_{DS} = V_{GS}, I_D = -250μA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	59	90	mΩ	V_{GS} = -4.5V, I_D = -2.9A
		—	76	137		V_{GS} = -2.5V, I_D = -2.3A
Diode Forward Voltage	V_{SD}	—	-0.65	-1.2	V	V_{GS} = 0V, I_S = -3.0A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	881	—	pF	V_{DS} = -10V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	84	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	67	—	pF	
Gate Resistance	R_g	—	14.3	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = -4.5V)	Q_g	—	11	—	nC	V_{DS} = -10V, I_D = -3.7A
Total Gate Charge (V_{GS} = -8V)		—	18	—	nC	
Gate-Source Charge	Q_{gs}	—	1.5	—	nC	
Gate-Drain Charge	Q_{gd}	—	2.3	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	5.0	—	ns	V_{DD} = -10V, V_{GS} = -4.5V, R_L = 3.3Ω, R_G = 1Ω
Turn-On Rise Time	t_r	—	9.5	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	29.7	—	ns	
Turn-Off Fall Time	t_f	—	20.4	—	ns	
Body Diode Reverse Recovery Time	trr	—	23.6	—	nS	I_S = -3.0A, dI/dt = 100A/μs
Body Diode Reverse Recovery Charge	Qrr	—	11.4	—	nC	I_S = -3.0A, dI/dt = 100A/μs

Notes: 6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.

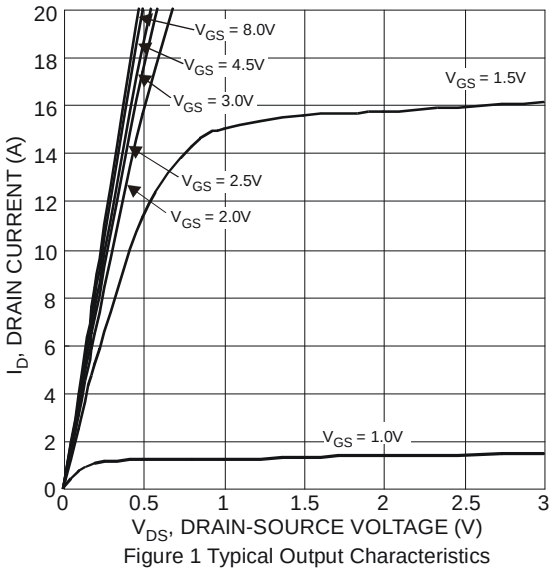


Figure 1 Typical Output Characteristics

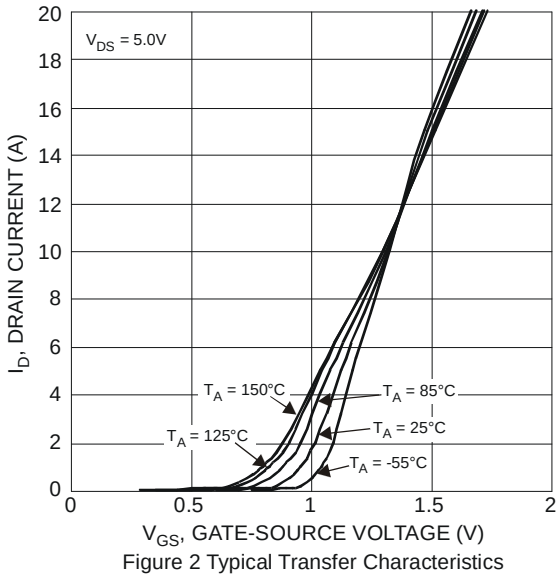


Figure 2 Typical Transfer Characteristics

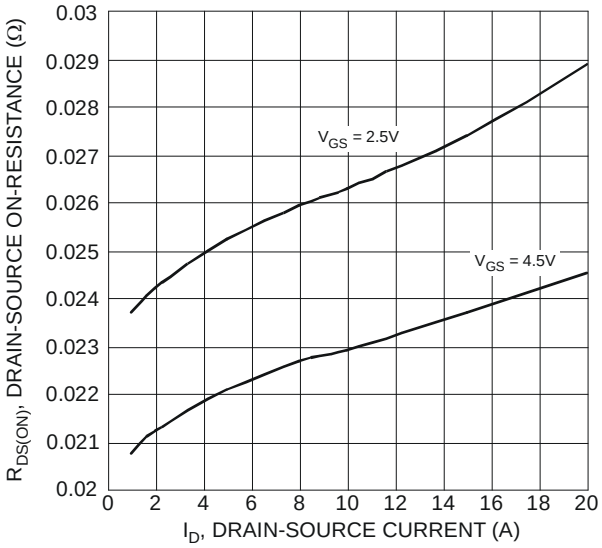


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

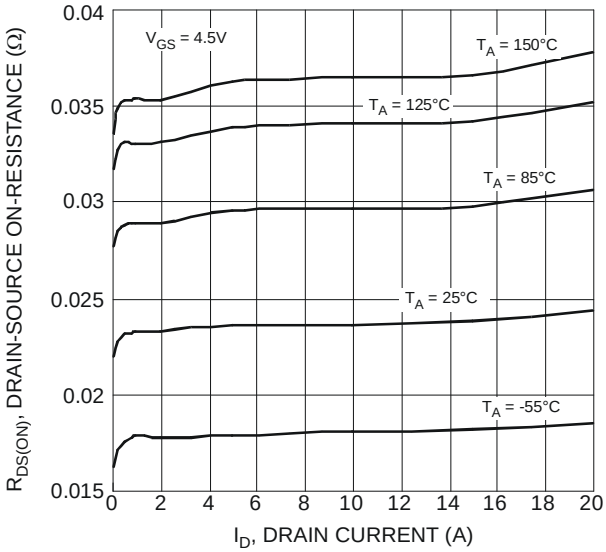


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

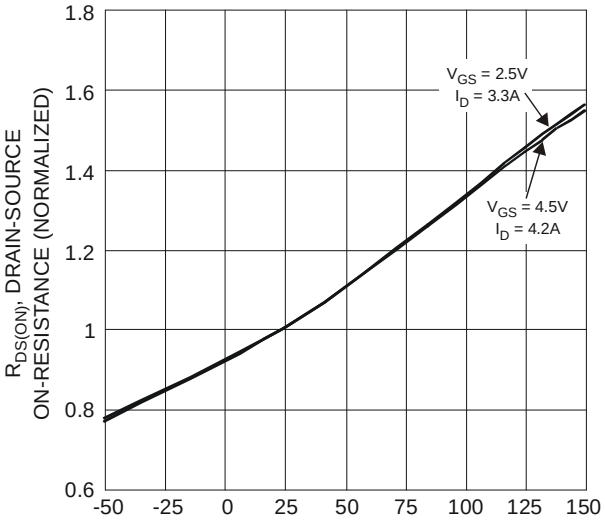


Figure 5 On-Resistance Variation with Temperature

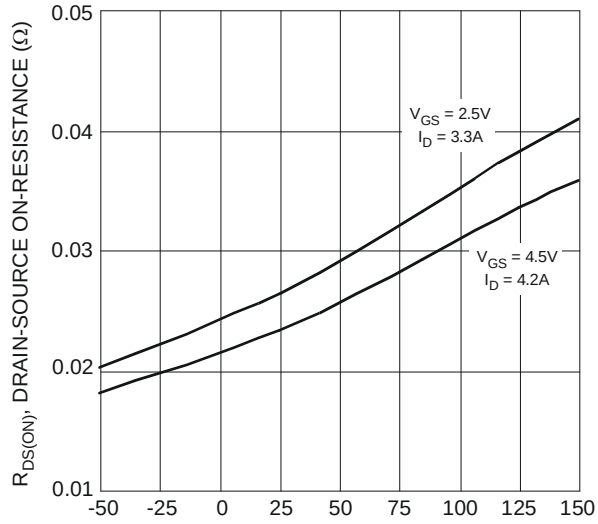


Figure 6 On-Resistance Variation with Temperature

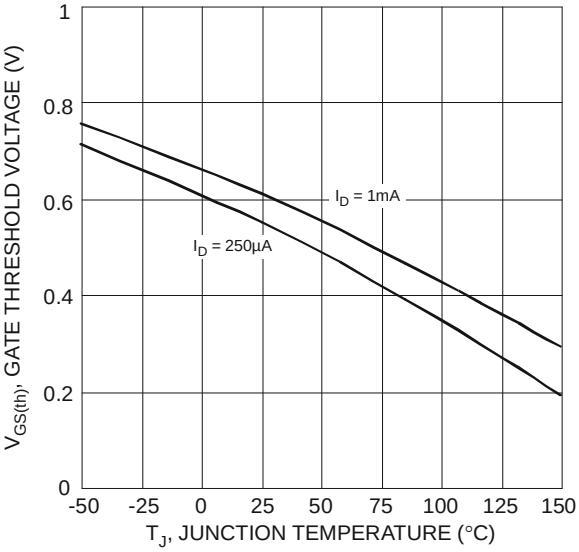


Figure 7 Gate Threshold Variation vs. Ambient Temperature

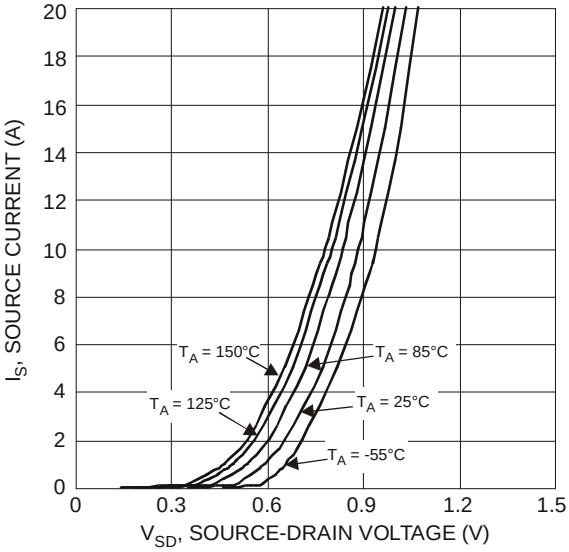


Figure 8 Diode Forward Voltage vs. Current

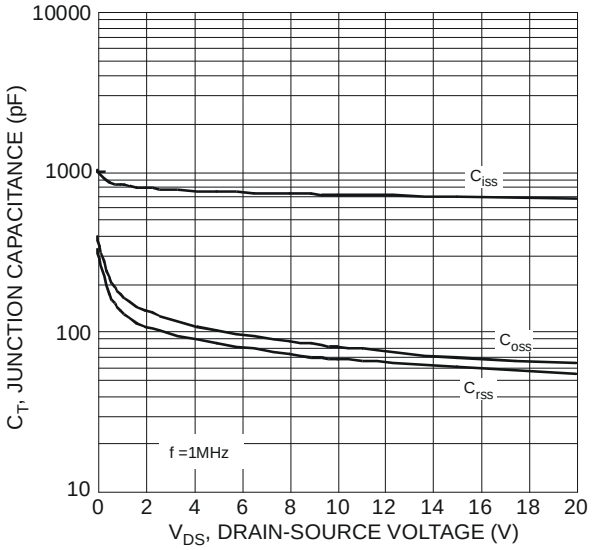


Figure 9 Typical Junction Capacitance

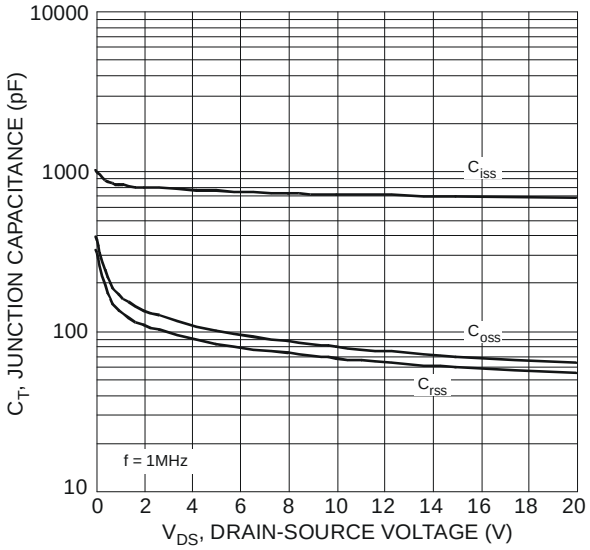


Figure 10 Typical Junction Capacitance

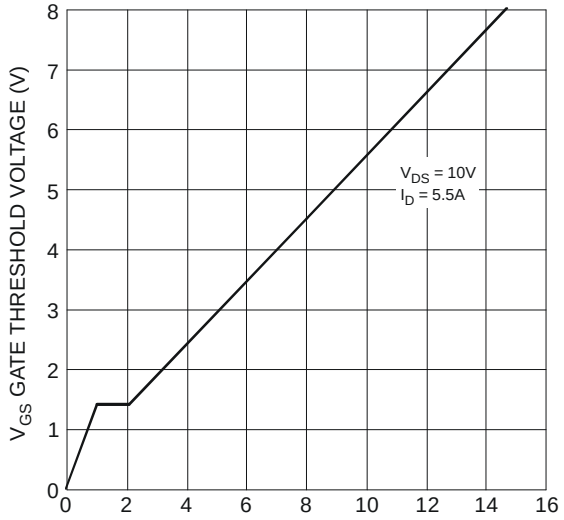


Figure 11 Gate Charge

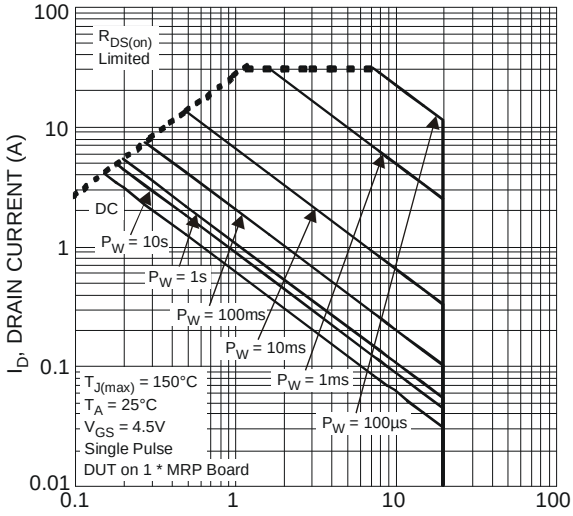


Figure 12 SOA, Safe Operation Area

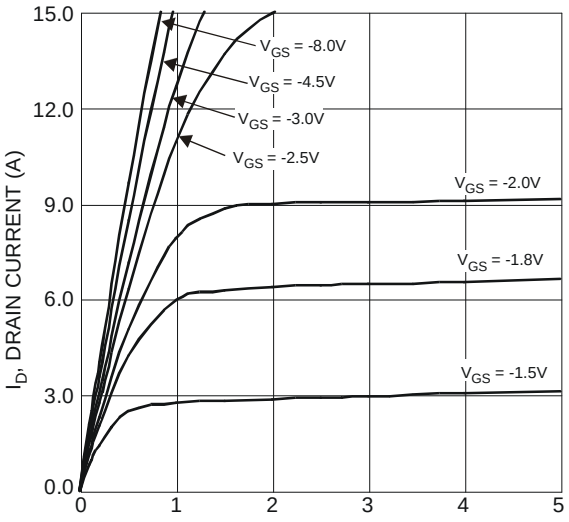


Figure 13 Typical Output Characteristics

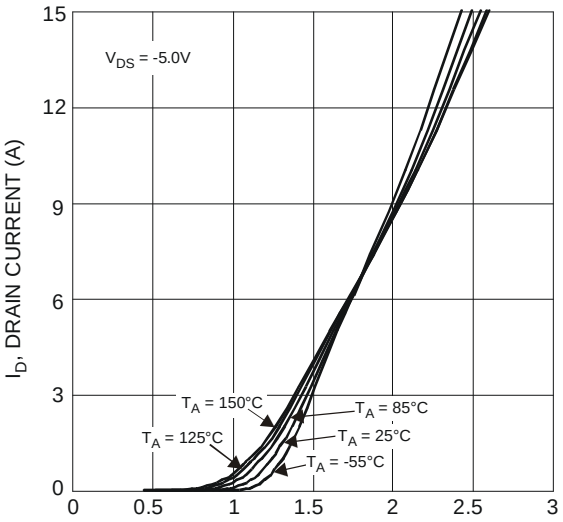


Figure14 Typical Transfer Characteristics

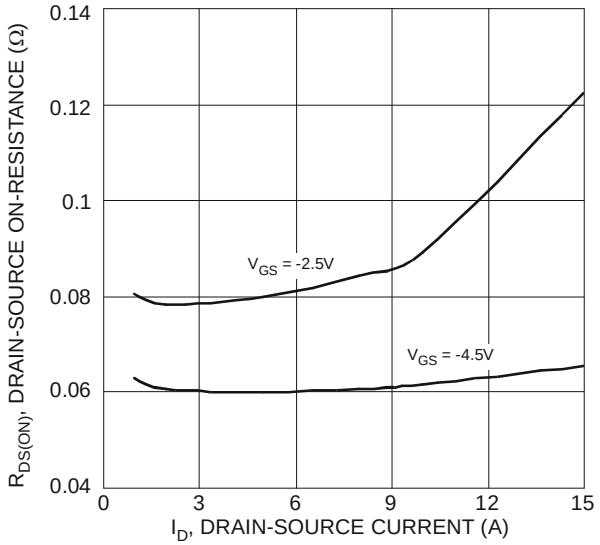


Figure 15 Typical On-Resistance vs. Drain Current and Gate Voltage

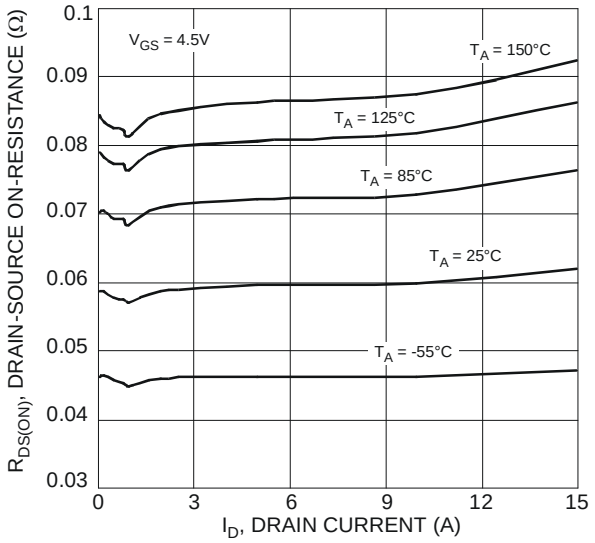


Figure 16 Typical On-Resistance vs. Drain Current and Temperature

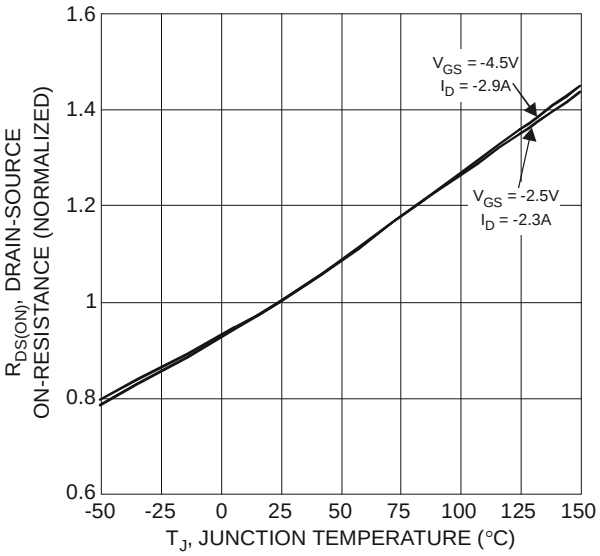


Figure 17 On-Resistance Variation with Temperature

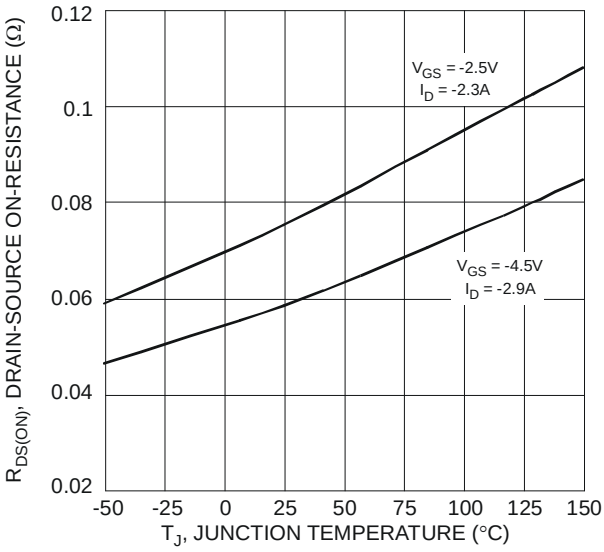


Figure 18 On-Resistance Variation with Temperature

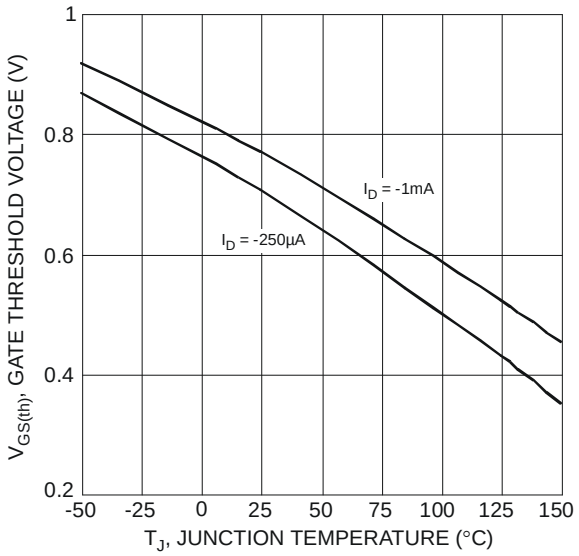


Figure 19 Gate Threshold Variation vs. Ambient Temperature

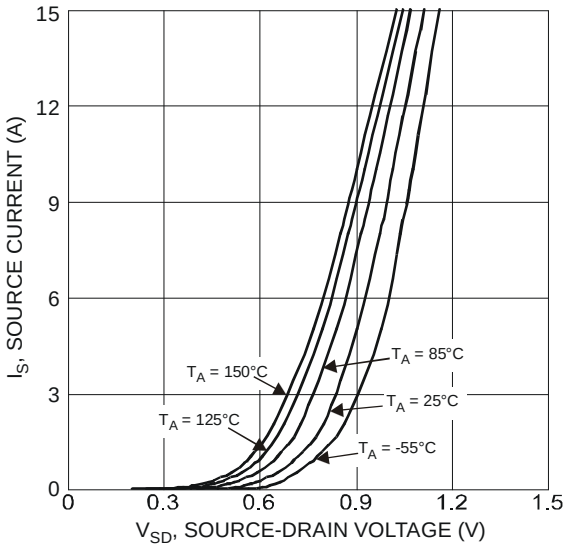


Figure 20 Diode Forward Voltage vs. Current

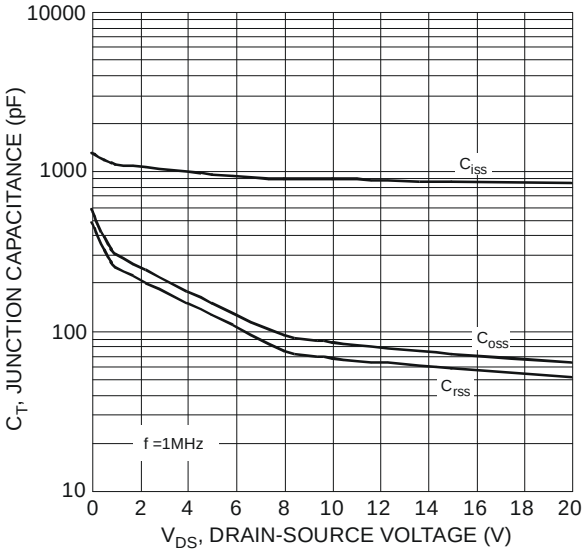


Figure 21 Typical Junction Capacitance

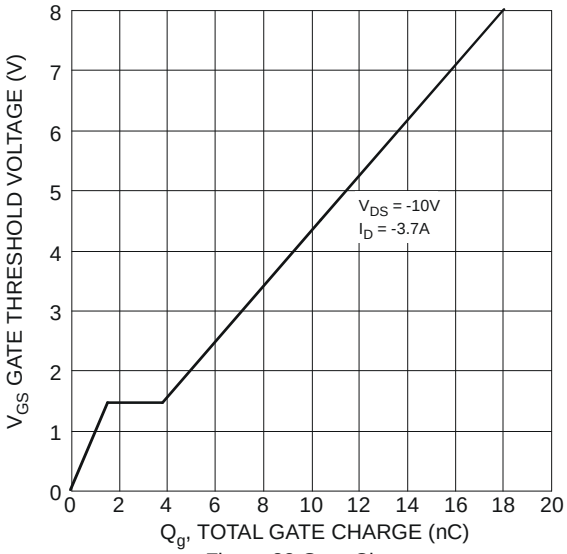


Figure 22 Gate Charge

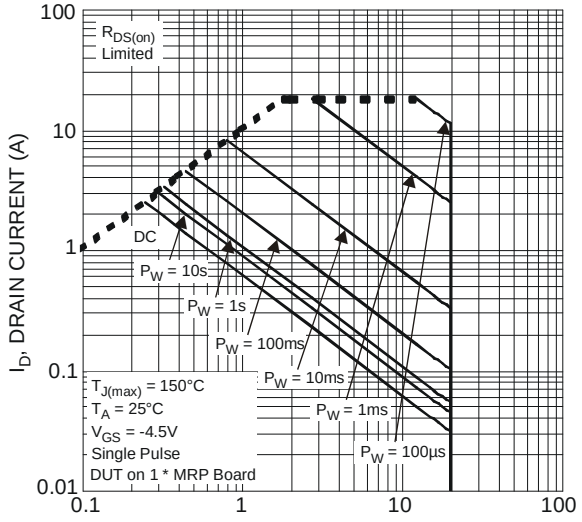


Figure 23 SOA, Safe Operation Area

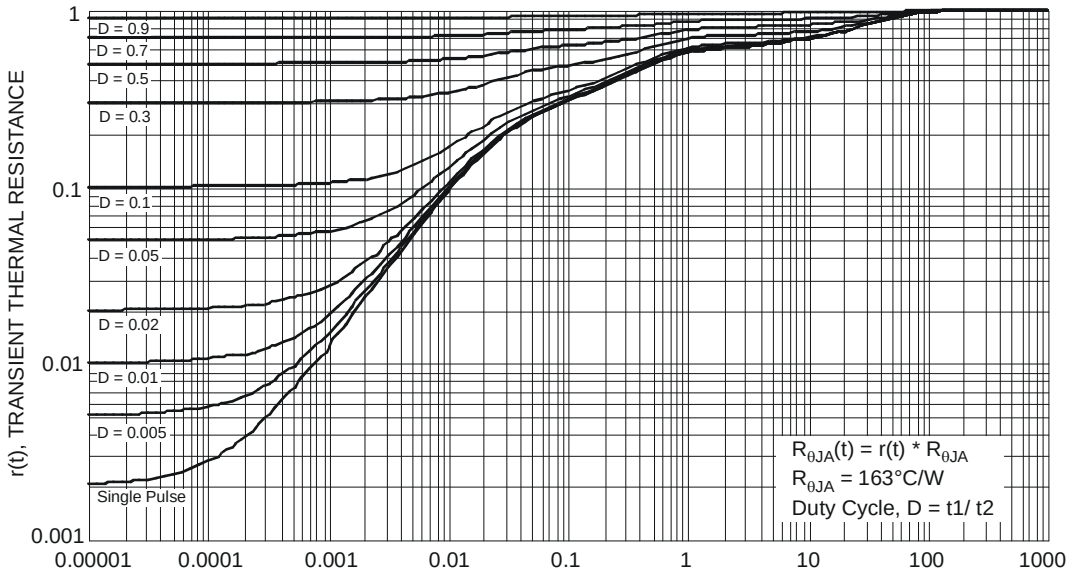
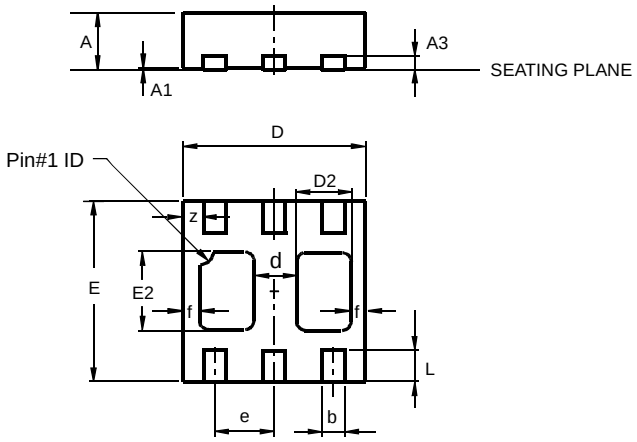


Figure 24 Transient Thermal Resistance

Package Outline Dimensions

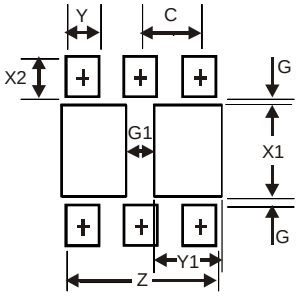
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the version.



U-DFN2020-6 Type B			
Dim	**Min**	**Max**	**Typ**
A	0.545	0.605	0.575
A1	0	0.05	0.02
A3	—	—	0.13
b	0.20	0.30	0.25
D	1.95	2.075	2.00
d	—	—	0.45
D2	0.50	0.70	0.60
e	—	—	0.65
E	1.95	2.075	2.00
E2	0.90	1.10	1.00
f	—	—	0.15
L	0.25	0.35	0.30
z	—	—	0.225
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	1.67
G	0.20
G1	0.40
X1	1.0
X2	0.45
Y	0.37
Y1	0.70
C	0.65

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1. are intended to implant into the body, or

2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

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Адрес: 105318, г.Москва, ул.Щербаковская д.3, офис 1107

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Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

http://moschip.ru/get-element

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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